Weimin M Chen

List of Publications by Year
in descending order

		61857	66788
459 papers	9,258 citations	43 h-index	78 g-index
468 all docs	468 docs citations	468 times ranked	7745 citing authors

#	Article	IF	Citations
1	Semi-metallic polymers. Nature Materials, 2014, 13, 190-194.	13.3	722
2	Design rules for minimizing voltage losses in high-efficiency organic solar cells. Nature Materials, 2018, 17, 703-709.	13.3	701
3	Mechanism for low-temperature photoluminescence in GaNAs/GaAs structures grown by molecular-beam epitaxy. Applied Physics Letters, 1999, 75, 501-503.	1.5	252
4	Silicon vacancy related defect in 4H and 6H SiC. Physical Review B, 2000, 61, 2613-2620.	1.1	223
5	Direct determination of electron effective mass in GaNAs/GaAs quantum wells. Applied Physics Letters, 2000, 77, 1843.	1.5	172
6	Electronic Properties of Ga(In)NAs Alloys. MRS Internet Journal of Nitride Semiconductor Research, 2001, 6, 1.	1.0	169
7	Mechanism responsible for the semiâ€insulating properties of lowâ€temperatureâ€grown GaAs. Applied Physics Letters, 1994, 65, 3002-3004.	1.5	140
8	ZnO Doped With Transition Metal Ions. IEEE Transactions on Electron Devices, 2007, 54, 1040-1048.	1.6	137
9	A high-conductivity n-type polymeric ink for printed electronics. Nature Communications, 2021, 12, 2354.	5.8	120
10	Wide bandgap GaN-based semiconductors for spintronics. Journal of Physics Condensed Matter, 2004, 16, R209-R245.	0.7	117
11	Oxygen and zinc vacancies in as-grown ZnO single crystals. Journal Physics D: Applied Physics, 2009, 42, 175411.	1.3	117
12	Ground-state electron transfer in all-polymer donorâ€“acceptor heterojunctions. Nature Materials, 2020, 19, 738-744.	13.3	111
13	Electron effective masses in 4H SiC. Applied Physics Letters, 1995, 66, 1074-1076.	1.5	109
14	Mechanism for rapid thermal annealing improvements in undoped GaNxAs1â^'x/GaAs structures grown by molecular beam epitaxy. Applied Physics Letters, 2000, 77, 2325-2327.	1.5	95
15	Influence of conduction-band nonparabolicity on electron confinement and effective mass inGaNxAs1â^'xâ^•GaAsquantum wells. Physical Review B, 2004, 69, .	1.1	94
16	Room-temperature defect-engineered spin filter based on a non-magnetic semiconductor. Nature Materials, 2009, 8, 198-202.	13.3	94
17	Ferromagnetism in Transition-Metal Doped ZnO. Journal of Electronic Materials, 2007, 36, 462-471.	1.0	90
18	Time-resolved studies of photoluminescence in GaNxP1â^'x alloys: Evidence for indirect-direct band gap crossover. Applied Physics Letters, 2002, 81, 52-54.	1.5	83

#	Article	IF	Citations
19	Electronic structure of the neutral silicon vacancy in4Hand6HSiC. Physical Review B, 2000, 62, 16555-16560.	1.1	82
20	Electron effective masses and mobilities in highâ€purity 6Hâ€“SiC chemical vapor deposition layers. Applied Physics Letters, 1994, 65, 3209-3211.	1.5	80
21	Determination of the electron effective-mass tensor in 4HSiC. Physical Review B, 1996, 53, 15409-15412.	1.1	77
22	A Freeâ€Standing Highâ€Output Power Density Thermoelectric Device Based on Structureâ€Ordered PEDOT:PSS. Advanced Electronic Materials, 2018, 4, 1700496.	2.6	73
23	Band gap properties of Zn1âˆ’xCdxO alloys grown by molecular-beam epitaxy. Applied Physics Letters, 2006, 89, 151909.	1.5	71
24	Trapâ€Assisted Recombination via Integer Charge Transfer States in Organic Bulk Heterojunction Photovoltaics. Advanced Functional Materials, 2014, 24, 6309-6316.	7.8	70
25	Phosphorus antisite defects in low-temperature InP. Physical Review B, 1993, 47, 4111-4114.	1.1	63
26	Formation of nonradiative defects in molecular beam epitaxial GaNxAs1âˆ’x studied by optically detected magnetic resonance. Applied Physics Letters, 2001, 79, 3089-3091.	1.5	63
27	Radiative recombination mechanism in GaNxP1âˆ’x alloys. Applied Physics Letters, 2002, 80, 1740-1742.	1.5	62
28	Photoluminescence of GaN: Effect of electron irradiation. Applied Physics Letters, 1998, 73, 2968-2970.	1.5	60
29	Effect of growth temperature on photoluminescence of GaNAs/GaAs quantum well structures. Applied Physics Letters, 1999, 75, 3781-3783.	1.5	59
30	Type I band alignment in theGaNxAs1âˆ’x/GaAsquantum wells. Physical Review B, 2000, 63, .	1.1	57
31	Dominant recombination centers in Ga(In)NAs alloys: Ga interstitials. Applied Physics Letters, 2009, 95, .	1.5	57
32	Signature of an intrinsic point defect inGaNxAs1âˆ’x. Physical Review B, 2001, 63, .	1.1	56
33	Nearâ€Infrared Lightâ€Responsive Cuâ€Doped Cs₂AgBiBr₆. Advanced Functional Materials, 2020, 30, 2005521.	7.8	56
34	Magnetizing lead-free halide double perovskites. Science Advances, 2020, 6, .	4.7	56
35	Hydrogen-induced improvements in optical quality of GaNAs alloys. Applied Physics Letters, 2003, 82, 3662-3664.	1.5	55
36	Applications of optically detected magnetic resonance in semiconductor layered structures. Thin Solid Films, 2000, 364, 45-52.	0.8	54

#	Article	IF	Citations
37	Nitrogen passivation induced by atomic hydrogen:â€ƒTheGaP1â^'yNycase. Physical Review B, 2003, 67, .	1.1	53
38	Optical detection of cyclotron resonance for characterization of recombination processes in semiconductors. Critical Reviews in Solid State and Materials Sciences, 1994, 19, 241-301.	6.8	52
39	Zinc-Vacancyâ€"Donor Complex: A Crucial Compensating Acceptor in ZnO. Physical Review Applied, 2014, 2, .	1.5	51
40	High quality 4Hâ€SiC epitaxial layers grown by chemical vapor deposition. Applied Physics Letters, 1995, 66, 1373-1375.	1.5	50
41	Analysis of band anticrossing inGaNxP1â^'xalloys. Physical Review B, 2004, 70, .	1.1	50
42	Dilute Nitride Nanowire Lasers Based on a GaAs/GaNAs Core/Shell Structure. Nano Letters, 2017, 17, 1775-1781.	4.5	45
43	Recombination processes in N-containing IIIâ€"V ternary alloys. Solid-State Electronics, 2003, 47, 467-475.	0.8	44
44	Effect of Backbone Regiochemistry on Conductivity, Charge Density, and Polaron Structure of n-Doped Donorâ€"Acceptor Polymers. Chemistry of Materials, 2019, 31, 3395-3406.	3.2	44
45	Direct observation of intercenter charge transfer in dominant nonradiative recombination channels in silicon. Physical Review Letters, 1991, 67, 1914-1917.	2.9	43
46	Ligand hyperfine interaction at the neutral silicon vacancy in 4H- and6Hâ^'SiC. Physical Review B, 2002, 66, .	1.1	43
47	Magneto-optical and light-emission properties of IIIÂAsÂN semiconductors. Semiconductor Science and Technology, 2002, 17, 815-822.	1.0	42
48	Er/O and Er/F doping during molecular beam epitaxial growth of Si layers for efficient 1.54 Î¼m light emission. Applied Physics Letters, 1997, 70, 3383-3385.	1.5	41
49	Hole effective masses in4Hâ€,SiC. Physical Review B, 2000, 61, R10544-R10546.	1.1	41
50	Sequential Doping of Ladder-Type Conjugated Polymers for Thermally Stable n-Type Organic Conductors. ACS Applied Materials & Interfaces, 2020, 12, 53003-53011.	4.0	41
51	Observation of rapid direct charge transfer between deep defects in silicon. Physical Review Letters, 1994, 72, 2939-2942.	2.9	40
52	Microscopic identification and electronic structure of a di-hydrogenâ€"vacancy complex in silicon by optical detection of magnetic resonance. Physical Review Letters, 1990, 64, 3042-3045.	2.9	38
53	Origin ofnâ€type conductivity of lowâ€temperature grown InP. Journal of Applied Physics, 1994, 76, 600-602.	1.1	38
54	Optically detected magnetic resonance studies of defects in electron-irradiated 3C SiC layers. Physical Review B, 1997, 55, 2863-2866.	1.1	38

#	Article	IF	Citations
55	Properties of Ga-interstitial defects inAlxGa1â'xNyP1â'y. Physical Review B, 2005, 71, .	1.1	37
56	Photoluminescence and Zeeman effect in chromium-doped 4H and 6H SiC. Journal of Applied Physics, 1999, 86, 4348-4353.	1.1	36
57	On the origin of spin loss in GaMnN/InGaN light-emitting diodes. Applied Physics Letters, 2004, 84, 2599-2601.	1.5	36
58	Turning ZnO into an Efficient Energy Upconversion Material by Defect Engineering. Advanced Functional Materials, 2014, 24, 3760-3764.	7.8	36
59	Growth and characterization of dilute nitride GaNxP1â^'x nanowires and GaNxP1â^'x/GaNyP1â^'y core/shell nanowires on Si (111) by gas source molecular beam epitaxy. Applied Physics Letters, 2014, 105, .	1.5	36
60	Spin injection and helicity control of surface spin photocurrent in a three dimensional topological insulator. Nature Communications, 2017, 8, 15401.	5.8	36
61	Evidence for coupling between exciton emissions and surface plasmon in Ni-coated ZnO nanowires. Nanotechnology, 2012, 23, 425201.	1.3	35
62	Suppression of non-radiative surface recombination by N incorporation in GaAs/GaNAs core/shell nanowires. Scientific Reports, 2015, 5, 11653.	1.6	35
63	Temperature dependence of the GaNxP1â^'x band gap and effect of band crossover. Applied Physics Letters, 2002, 81, 3984-3986.	1.5	34
64	Defects in N, O and N, Zn implanted ZnO bulk crystals. Journal of Applied Physics, 2013, 113, .	1.1	34
65	Electronic structure of bound excitons in semiconductors. Physica B: Physics of Condensed Matter & C: Atomic, Molecular and Plasma Physics, Optics, 1987, 146, 256-285.	0.9	33
66	Exciton spin relaxation in diluted magnetic semiconductorZn1â^'xMnxSe/CdSesuperlattices: Effect of spin splitting and role of longitudinal optical phonons. Physical Review B, 2003, 67, .	1.1	33
67	Efficient room-temperature nuclear spin hyperpolarization of a defect atom in a semiconductor. Nature Communications, 2013, 4, 1751.	5.8	33
68	Impact of Singly Occupied Molecular Orbital Energy on the n-Doping Efficiency of Benzimidazole Derivatives. ACS Applied Materials & Interfaces, 2019, 11, 37981-37990.	4.0	32
69	Electron spin filtering by thin GaNAs/GaAs multiquantum wells. Applied Physics Letters, 2010, 96, .	1.5	31
70	Dominant recombination center in electronâ€irradiated 3CSiC. Journal of Applied Physics, 1996, 79, 3784-3786.	1.1	30
71	Optically detected magnetic resonance studies of intrinsic defects in 6H-SiC. Semiconductor Science and Technology, 1999, 14, 1141-1146.	1.0	30
72	Defects in dilute nitrides. Journal of Physics Condensed Matter, 2004, 16, S3027-S3035.	0.7	30

#	Article	IF	Citations
73	Long lifetime of free excitons in ZnO tetrapod structures. Applied Physics Letters, 2010, 96, .	1.5	30
74	Mechanism for radiative recombination and defect properties of GaP/GaNP core/shell nanowires. Applied Physics Letters, 2012, 101, 163106.	1.5	30
75	Spectroelectrochemistry and Nature of Charge Carriers in Selfâ€Doped Conducting Polymer. Advanced Electronic Materials, 2017, 3, 1700096.	2.6	30
76	Mechanism for thermal quenching of luminescence in SiGe/Si structures grown by molecular beam epitaxy: Role of nonradiative defects. Applied Physics Letters, 1997, 71, 3676-3678.	1.5	29
77	Tunable laser spectroscopy of spin injection in ZnMnSe/ZnCdSe quantum structures. Applied Physics Letters, 2002, 81, 2196-2198.	1.5	29
78	Enhancement of polymer endurance to UV light by incorporation of semiconductor nanoparticles. Nanoscale Research Letters, 2015, 10, 81.	3.1	29
79	Nonequilibrium site distribution governs charge-transfer electroluminescence at disordered organic heterointerfaces. Proceedings of the National Academy of Sciences of the United States of America, 2019, 116, 23416-23425.	3.3	29
80	SiC â€" a semiconductor for high-power, high-temperature and high-frequency devices. Physica Scripta, 1994, T54, 283-290.	1.2	28
81	Carbon-vacancy related defects in 4H- and 6H-SiC. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1999, 61-62, 202-206.	1.7	28
82	Optical characterization of III-nitrides. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 93, 112-122.	1.7	28
83	Near-Infrared Lasing at 1 Î¼m from a Dilute-Nitride-Based Multishell Nanowire. Nano Letters, 2019, 19, 885-890.	4.5	28
84	Vibronic coherence contributes to photocurrent generation in organic semiconductor heterojunction diodes. Nature Communications, 2020, 11, 617.	5.8	28
85	Possible lifetimeâ€limiting defect in 6H SiC. Applied Physics Letters, 1994, 65, 2687-2689.	1.5	27
86	Structural properties of a GaNxP1â^'x alloy: Raman studies. Applied Physics Letters, 2001, 78, 3959-3961.	1.5	27
87	Origin of radiative recombination and manifestations of localization effects in GaAs/GaNAs core/shell nanowires. Applied Physics Letters, 2014, 105, .	1.5	27
88	Room-temperature electron spin polarization exceeding 90% in an opto-spintronic semiconductor nanostructure via remote spin filtering. Nature Photonics, 2021, 15, 475-482.	15.6	27
89	Transfer processes for excitons bound to complex defects in GaP studied by optical detection of magnetic resonance. Physical Review B, 1988, 37, 2570-2577.	1.1	26
90	Role of free carriers in the application of optically detected magnetic resonance for studies of defects in silicon. Applied Physics A: Solids and Surfaces, 1991, 53, 130-135.	1.4	26

#	Article	IF	Citations
91	Optically detected cyclotron resonance investigations on4Hand6HSiC: Band-structure and transport properties. Physical Review B, 2000, 61, 4844-4849.	1.1	26
92	Identification of a dominant mechanism for optical spin injection from a diluted magnetic semiconductor: Spin-conserving energy transfer via localized excitations. Physical Review B, 2005, 72, .	1.1	26
93	Efficient upconversion of photoluminescence via two-photon absorption in bulk and nanorod ZnO. Applied Physics B: Lasers and Optics, 2012, 108, 919-924.	1.1	26
94	Energy Upconversion in GaP/GaNP Core/Shell Nanowires for Enhanced Nearâ€Infrared Light Harvesting. Small, 2014, 10, 4403-4408.	5.2	26
95	Zero-field optical detection of magnetic resonance on a metastable sulfur-pair-related defect in silicon: Evidence for a Cu constituent. Physical Review B, 1992, 46, 12316-12322.	1.1	25
96	Experimental evidence for N-induced strong coupling of host conduction band states inGaNxP1â^'x:â€ƒInsight into the dominant mechanism for giant band-gap bowing. Physical Review B, 2004, 69, .	1.1	25
97	Point defects in dilute nitride III-Nâ€"As and III-Nâ€"P. Physica B: Condensed Matter, 2006, 376-377, 545-551.	1.3	25
98	Direct experimental evidence for unusual effects of hydrogen on the electronic and vibrational properties ofGaNxP1â^'xalloys: A proof for a general property of dilute nitrides. Physical Review B, 2004, 70, .	1.1	24
99	Charge Generation via Relaxed Charge-Transfer States in Organic Photovoltaics by an Energy-Disorder-Driven Entropy Gain. Journal of Physical Chemistry C, 2018, 122, 12640-12646.	1.5	24
100	Effective Masses in SiC Determined by Cyclotron Resonance Experiments. Physica Status Solidi A, 1997, 162, 79-93.	1.7	23
101	Efficient spin depolarization in ZnCdSe spin detector: an important factor limiting optical spin injection efficiency in ZnMnSeâ^•ZnCdSe spin light-emitting structures. Applied Physics Letters, 2004, 85, 5260-5262.	1.5	23
102	Mechanism for radiative recombination in ZnCdO alloys. Applied Physics Letters, 2007, 90, 261907.	1.5	23
103	Roomâ€Temperature Electron Spin Amplifier Based on Ga(In)NAs Alloys. Advanced Materials, 2013, 25, 738-742.	11.1	23
104	Dynamics of exciton-spin injection, transfer, and relaxation in self-assembled quantum dots of CdSe coupled with a diluted magnetic semiconductor layer ofZn0.80Mn0.20Se. Physical Review B, 2007, 75, .	1.1	22
105	Effects of hydrogen on the optical properties of ZnCdOâ^•ZnO quantum wells grown by molecular beam epitaxy. Applied Physics Letters, 2008, 92, 261912.	1.5	22
106	Origin of Strong Photoluminescence Polarization in GaNP Nanowires. Nano Letters, 2014, 14, 5264-5269.	4.5	22
107	Strongly polarized quantum-dot-like light emitters embedded in GaAs/GaNAs core/shell nanowires. Nanoscale, 2016, 8, 15939-15947.	2.8	22
108	Control of spin functionality in ZnMnSe-based structures: Spin switching versus spin alignment. Applied Physics Letters, 2003, 82, 1700-1702.	1.5	21

#	Article	IF	Citations
109	Paramagnetic centers in detonation nanodiamonds studied by CW and pulse EPR. Chemical Physics Letters, 2010, 493, 319-322.	1.2	21
110	Efficient nitrogen incorporation in ZnO nanowires. Scientific Reports, 2015, 5, 13406.	1.6	21
111	Effect of Side Groups on the Photovoltaic Performance Based on Porphyrinâ€"Perylene Bisimide Electron Acceptors. ACS Applied Materials & Interfaces, 2018, 10, 32454-32461.	4.0	21
112	Intrinsic Doping: A New Approach forn-Type Modulation Doping in InP-Based Heterostructures. Physical Review Letters, 1996, 77, 2734-2737.	2.9	20
113	As-Grown 4H-SiC Epilayers with Magnetic Properties. Materials Science Forum, 2004, 457-460, 747-750.	0.3	20
114	Efficient spin relaxation in InGaNâˆ•GaN and InGaNâˆ•GaMnN quantum wells: An obstacle to spin detection. Applied Physics Letters, 2005, 87, 192107.	1.5	20
115	Raman spectroscopy of GaP/GaNP core/shell nanowires. Applied Physics Letters, 2014, 105, 193102.	1.5	20
116	Interfacial bonding in a CdS/PVA nanocomposite: A Raman scattering study. Journal of Colloid and Interface Science, 2015, 452, 33-37.	5.0	20
117	Optimizing GaNP Coaxial Nanowires for Efficient Light Emission by Controlling Formation of Surface and Interfacial Defects. Nano Letters, 2015, 15, 242-247.	4.5	20
118	Electronic properties of low-temperature InP. Journal of Electronic Materials, 1993, 22, 1487-1490.	1.0	19
119	Strong room-temperature optical and spin polarization in InAs/GaAs quantum dot structures. Applied Physics Letters, 2011, 98, .	1.5	19
120	Effects of Polytypism on Optical Properties and Band Structure of Individual Ga(N)P Nanowires from Correlative Spatially Resolved Structural and Optical Studies. Nano Letters, 2015, 15, 4052-4058.	4.5	19
121	PGa-antisite-related neutral complex defect in GaP studied with optically detected magnetic resonance. Physical Review B, 1987, 36, 5058-5061.	1.1	18
122	Optically detected magnetic resonance studies of low-temperature InP. Journal of Electronic Materials, 1993, 22, 1491-1494.	1.0	18
123	Photoluminescence of the two-dimensional hole gas inp-type Î´-doped Si layers. Physical Review B, 1996, 53, 9587-9590.	1.1	18
124	Identification ofGa-interstitial defects inGaNyP1âˆ'yandAlxGa1âˆ'xNyP1âˆ'y. Physical Review B, 2004, 70, .	1.1	18
125	Dominant factors limiting efficiency of optical spin detection in ZnO-based materials. Applied Physics Letters, 2008, 92, 092103.	1.5	18
126	Effects of stoichiometry on defect formation in ZnO epilayers grown by molecular-beam epitaxy: An optically detected magnetic resonance study. Journal of Applied Physics, 2008, 103, 023712.	1.1	18

#	Article	IF	Citations
127	Catalytic conversion of C2-C3 alcohols on detonation nanodiamond and its modifications. Russian Journal of Physical Chemistry A, 2012, 86, 26-31.	0.1	18
128	Effects of Ni-coating on ZnO nanowires: A Raman scattering study. Journal of Applied Physics, 2013, 113, 214302.	1.1	18
129	Fine Structure and Spin Dynamics of Linearly Polarized Indirect Excitons in Two-Dimensional CdSe/CdTe Colloidal Heterostructures. ACS Nano, 2019, 13, 10140-10153.	7.3	18
130	Spontaneous exciton dissociation enables spin state interconversion in delayed fluorescence organic semiconductors. Nature Communications, 2021, 12, 6640.	5.8	18
131	On the Origin of Seebeck Coefficient Inversion in Highly Doped Conducting Polymers. Advanced Functional Materials, 2022, 32, .	7.8	18
132	Optically detected magnetic resonance investigation of a deep Li-related complex in GaP. Physical Review B, 1985, 32, 6650-6654.	1.1	17
133	Steady-state level-anticrossing spectra for bound-exciton triplets associated with complex defects in semiconductors. Physical Review B, 1990, 41, 5746-5755.	1.1	17
134	Influence of ion bombardment on Si and SiGe films during molecular beam epitaxy growth. Applied Physics Letters, 1996, 68, 238-240.	1.5	17
135	Identification of an isolated arsenic antisite defect in GaAsBi. Applied Physics Letters, 2014, 104, 052110.	1.5	17
136	Optical properties and excitation-induced distortions of a trigonal Cu-related neutral complex with a bound exciton at 2.26 eV in ZnTe. Physical Review B, 1986, 34, 8656-8666.	1.1	16
137	Optical investigation of Fermi-edge singularities inAl0.35Ga0.65As/GaAs heterostructures. Physical Review B, 1992, 46, 4352-4355.	1.1	16
138	Identification of Grown-In Efficient Nonradiative Recombination Centers in Molecular Beam Epitaxial Silicon. Physical Review Letters, 1996, 77, 4214-4217.	2.9	16
139	UD-3 defect in4H,6H,and15RSiC: Electronic structure and phonon coupling. Physical Review B, 2002, 66, .	1.1	16
140	Optical study of spin injection dynamics in InGaNâˆ•GaN quantum wells with GaMnN injection layers. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2004, 22, 2668.	1.6	16
141	Efficiency of optical spin injection and spin loss from a diluted magnetic semiconductor ZnMnSe to CdSe nonmagnetic quantum dots. Physical Review B, 2008, 77, .	1.1	16
142	Dynamics of donor bound excitons in ZnO. Applied Physics Letters, 2013, 102, .	1.5	16
143	Room-temperature polarized spin-photon interface based on a semiconductor nanodisk-in-nanopillar structure driven by few defects. Nature Communications, 2018, 9, 3575.	5.8	16
144	GaAs/GaNAs core-multishell nanowires with nitrogen composition exceeding 2%. Applied Physics Letters, 2018, 113, .	1.5	16

#	Article	IF	Citations
145	Measurements of Strain and Bandgap of Coherently Epitaxially Grown Wurtzite InAsPâ€"InP Coreâ€"Shell Nanowires. Nano Letters, 2019, 19, 2674-2681.	4.5	16
146	Thermal-annealing effects on energy level alignment at organic heterojunctions and corresponding voltage losses in all-polymer solar cells. Nano Energy, 2020, 72, 104677.	8.2	16
147	Gaiself-interstitial-related defect in GaP studied by optically detected magnetic resonance. Physical Review B, 1989, 40, 1365-1368.	1.1	15
148	Similarity between the 0.88-eV photoluminescence in GaN and the electron-capture emission of theOPdonor in GaP. Physical Review B, 1998, 58, R13351-R13354.	1.1	15
149	Mechanism of radiative recombination in acceptor-doped bulk GaN crystals. Physica B: Condensed Matter, 1999, 273-274, 39-42.	1.3	15
150	Optical properties of GaNAs/GaAs structures. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 82, 143-147.	1.7	15
151	Modeling of band gap properties of GaInNP alloys lattice matched to GaAs. Applied Physics Letters, 2006, 88, 031907.	1.5	15
152	Optical characterization of ZnMnO-based dilute magnetic semiconductor structures. Journal of Vacuum Science & Technology B, 2006, 24, 259.	1.3	15
153	Defect properties of ZnO nanowires revealed from an optically detected magnetic resonance study. Nanotechnology, 2013, 24, 015701.	1.3	15
154	Magneto-optical properties of Cr3+ in Î²-Ga2O3. Applied Physics Letters, 2021, 119, .	1.5	15
155	Electronic properties of an electron-attractive complex neutral defect in GaAs. Physical Review B, 1986, 33, 4424-4427.	1.1	14
156	Properties of shallow Li-related donors in GaP from optically detected magnetic resonance. Physical Review B, 1986, 33, 8246-8253.	1.1	14
157	The Neutral Silicon Vacancy in 6H and 4H SiC. Materials Science Forum, 1998, 264-268, 473-476.	0.3	14
158	Photoluminescence characterization of GaNAs/GaAs structures grown by molecular beam epitaxy. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2000, 75, 166-169.	1.7	14
159	Formation of Ga interstitials in (Al,In)yGa1â^'yNxP1â^'x alloys and their role in carrier recombination. Applied Physics Letters, 2004, 85, 2827-2829.	1.5	14
160	Formation of grown-in defects in molecular beam epitaxial Ga(In)NP: Effects of growth conditions and postgrowth treatments. Journal of Applied Physics, 2008, 103, 063519.	1.1	14
161	Electron spin control in dilute nitride semiconductors. Journal of Physics Condensed Matter, 2009, 21, 174211.	0.7	14
162	Electronic structure of a hole-attractive neutral Cu-related complex-defect bound exciton at 2.345 eV in ZnTe. Physical Review B, 1987, 35, 5722-5728.	1.1	13

#	Article	IF	Citations
163	Effect of momentum relaxation on exciton spin dynamics in diluted magnetic semiconductorZnMnSeâˆ•CdSesuperlattices. Physical Review B, 2005, 71, .	1.1	13
164	Photoluminescence upconversion in GaInNPâˆ•GaAs heterostructures grown by gas source molecular beam epitaxy. Journal of Applied Physics, 2006, 99, 073515.	1.1	13
165	Slowdown of light due to exciton-polariton propagation in ZnO. Physical Review B, 2011, 83, .	1.1	13
166	Kidneys From Standard-Criteria Donors With Different Severities of Terminal Acute Kidney Injury. Transplantation Proceedings, 2014, 46, 3335-3338.	0.3	13
167	Fabryâ€“Perot Microcavity Modes in Single GaP/GaNP Core/Shell Nanowires. Small, 2015, 11, 6331-6337.	5.2	13
168	Dilute nitrides-based nanowiresâ€"a promising platform for nanoscale photonics and energy technology. Nanotechnology, 2019, 30, 292002.	1.3	13
169	Competition between triplet pair formation and excimer-like recombination controls singlet fission yield. Cell Reports Physical Science, 2021, 2, 100339.	2.8	13
170	Optically detected magnetic resonance studies of the 1.911-eV Cu-related complex in GaP. Physical Review B, 1988, 37, 2558-2563.	1.1	12
171	Two deep (PGa-Cu)-related neutral complex defects in GaP studied with optically detected magnetic resonance. Physical Review B, 1988, 37, 2564-2569.	1.1	12
172	Mechanism of the configurational change of metastable defects in silicon. Physical Review Letters, 1993, 71, 416-419.	2.9	12
173	Optically detected magnetic-resonance study of a metastable selenium-related center in silicon. Physical Review B, 1995, 51, 2132-2136.	1.1	12
174	Spin injection in lateral InAs quantum dot structures by optical orientation spectroscopy. Nanotechnology, 2009, 20, 375401.	1.3	12
175	On the origin of suppression of free exciton no-phonon emission in ZnO tetrapods. Applied Physics Letters, 2010, 96, .	1.5	12
176	Effect of hyperfine-induced spin mixing on the defect-enabled spin blockade and spin filtering in GaNAs. Physical Review B, 2013, 87, .	1.1	12
177	Defect formation in GaAs/GaNxAs1-x core/shell nanowires. Applied Physics Letters, 2016, 109, .	1.5	12
178	Effects of Nitrogen Incorporation on Structural and Optical Properties of GaNAsP Nanowires. Journal of Physical Chemistry C, 2017, 121, 7047-7055.	1.5	12
179	Electronic structure of the 2.3149-eV complex defect in Ag-doped ZnTe. Physical Review B, 1987, 36, 4831-4835.	1.1	11
180	Strong effects of carrier concentration on the Fermi-edge singularity in modulation-doped InP/InxGa1âˆ’xAs heterostructures. Physical Review B, 1997, 55, 7052-7058.	1.1	11

#	Article	IF	Citations
181	Chromium in 4H and 6H SiC: Photoluminescence and Zeeman Studies. Materials Science Forum, 1998, 264-268, 603-606.	0.3	11
182	Ga-related defect in as-grown Zn-doped GaN: An optically detected magnetic resonance study. Physical Review B, 2000, 62, R10607-R10609.	1.1	11
183	Optically detected magnetic resonance studies of point defects in Ga(Al)NAs. Physical Review B, 2006, 73, .	1.1	11
184	Migration and luminescence enhancement effects of deuterium in ZnOâˆ•ZnCdO quantum wells. Applied Physics Letters, 2008, 92, .	1.5	11
185	Evidence for a phosphorus-related interfacial defect complex at a GaP/GaNP heterojunction. Physical Review B, 2010, 81, .	1.1	11
186	Polyol-thermal synthesis of silver nanowires for Hg2+ sensing detection. Journal of Nanoparticle Research, 2011, 13, 5087-5101.	0.8	11
187	Effects of Ultraviolet Light on Optical Properties of Colloidal CdS Nanoparticles Embedded in Polyvinyl Alcohol (PVA) Matrix. Advanced Science, Engineering and Medicine, 2012, 4, 394-400.	0.3	11
188	Role of the host polymer matrix in light emission processes in nano-CdS/poly vinyl alcohol composite. Thin Solid Films, 2013, 543, 11-15.	0.8	11
189	Anomalous spectral dependence of optical polarization and its impact on spin detection in InGaAs/GaAs quantum dots. Applied Physics Letters, 2014, 105, 132106.	1.5	11
190	Growth of isotopically enriched ZnO nanorods of excellent optical quality. Journal of Crystal Growth, 2015, 429, 6-12.	0.7	11
191	Electron paramagnetic resonance signatures of Co2+ and Cu2+ in <i>Î²</i> -Ga2O3. Applied Physics Letters, 2019, 115, .	1.5	11
192	Effect of Crystal Symmetry on the Spin States of Fe³⁺ and Vibration Modes in Lead-free Double-Perovskite Cs₂AgBi(Fe)Br₆. Journal of Physical Chemistry Letters, 2020, 11, 4873-4878.	2.1	11
193	Magnetic Resonance from a Metastable Sulfur-Pair-Related Complex Defect in Silicon. Materials Science Forum, 1992, 83-87, 251-256.	0.3	10
194	Magneto-optical studies of the 0.88-eV photoluminescence emission in electron-irradiated GaN. Physical Review B, 2000, 62, 16572-16577.	1.1	10
195	Optical and electrical characterization of (Ga,Mn)N/InGaN multiquantum well light-emitting diodes. Journal of Electronic Materials, 2004, 33, 467-471.	1.0	10
196	Effects of Strong Band-Tail States on Exciton Recombination Dynamics in Dilute Nitride GaP/GaNP Core/Shell Nanowires. Journal of Physical Chemistry C, 2018, 122, 19212-19218.	1.5	10
197	Electronic properties of a (Cu-Li)-related neutral complex defect with a bound exciton at 2.25 eV in GaP. Physical Review B, 1987, 36, 7948-7954.	1.1	9
198	Delayed optical detection of magnetic resonance for defects in Si and GaAs. Journal of Applied Physics, 1990, 68, 2506-2509.	1.1	9

#	Article	IF	Citations
199	Response to â€˜â€˜Comment on â€˜Mechanism responsible for the semiâ€insulating properties of lowâ€temperatureâ€grown GaAsâ€™â€‰â€™â€™ [Appl. Phys. Lett. 67, 1331 (1995)]. Applied Physics Letters, 1995, 67, 1333-1334.	1.5	9
200	Some critical issues on growth of high quality Si and SiGe films using a solid-source molecular beam epitaxy system. Journal of Crystal Growth, 1995, 157, 242-247.	0.7	9
201	Properties of deep photoluminescence bands in SiGe/Si quantum structures grown by molecular beam epitaxy. Applied Physics Letters, 1995, 67, 1642-1644.	1.5	9
202	Optical detection of quantum oscillations in InP/InGaAs quantum structures. Applied Physics Letters, 1996, 69, 809-811.	1.5	9
203	Deep luminescent centres in electron-irradiated 6H SiC. Diamond and Related Materials, 1997, 6, 1378-1380.	1.8	9
204	Chenet al.Reply:. Physical Review Letters, 1998, 80, 423-423.	2.9	9
205	Mechanism for Light Emission in GaNAs/GaAs Structures Grown by Molecular Beam Epitaxy. Physica Status Solidi (B): Basic Research, 1999, 216, 125-129.	0.7	9
206	A Complex Defect Related to the Carbon Vacancy in 4H and 6H SiC. Physica Scripta, 1999, T79, 46.	1.2	9
207	Evaluation of optical quality and defect properties of GaNxP1â^'x alloys lattice matched to Si. Applied Physics Letters, 2004, 85, 6347-6349.	1.5	9
208	Effects of rapid thermal annealing on optical properties of GaNxP1â^'xalloys grown by solid source molecular beam epitaxy. Semiconductor Science and Technology, 2005, 20, 353-356.	1.0	9
209	Density-dependent dynamics of exciton magnetic polarons inZnMnSeâ^•ZnSSetype-II quantum wells. Physical Review B, 2006, 73, .	1.1	9
210	Hydrogen passivation of nitrogen in GaNAs and GaNP alloys: How many H atoms are required for each N atom?. Applied Physics Letters, 2007, 90, 021920.	1.5	9
211	Effects of Ga doping on optical and structural properties of ZnO epilayers. Superlattices and Microstructures, 2009, 45, 413-420.	1.4	9
212	Donor bound excitons involving a hole from the B valence band in ZnO: Time resolved and magneto-photoluminescence studies. Applied Physics Letters, 2011, 99, 091909.	1.5	9
213	Effect of postgrowth hydrogen treatment on defects in GaNP. Applied Physics Letters, 2011, 98, 141920.	1.5	9
214	Efficient room-temperature spin detector based on GaNAs. Journal of Applied Physics, 2012, 111, 07C303.	1.1	9
215	Effect of the detonation nanodiamond surface on the catalytic activity of deposited nickel catalysts in the hydrogenation of acetylene. Russian Journal of Physical Chemistry A, 2013, 87, 1114-1120.	0.1	9
216	Optically detected magnetic resonance studies of point defects in quaternary GaNAsP epilayers grown by vapor phase epitaxy. Applied Physics Letters, 2013, 102, 021910.	1.5	9

#	Article	IF	Citations
217	Luminescent and Optically Detected Magnetic Resonance Studies of CdS/PVA Nanocomposite. Nanoscale Research Letters, 2017, 12, 130.	3.1	9
218	Effects of N implantation on defect formation in ZnO nanowires. Thin Solid Films, 2019, 687, 137449.	0.8	9
219	Molecular beam epitaxial growth of dilute nitride GaNAs and GaInNAs nanowires. Nanotechnology, 2019, 30, 244002.	1.3	9
220	Anomalously Strong Secondâ€Harmonic Generation in GaAs Nanowires via Crystalâ€Structure Engineering. Advanced Functional Materials, 2021, 31, 2104671.	7.8	9
221	Characterization of GaAs/AlGaAs heterojunctions by optical detection of cyclotron resonance. Surface Science, 1990, 229, 484-487.	0.8	8
222	Optically detected impact-ionization-related chaotic oscillations inGa0.47In0.53As. Physical Review B, 1991, 44, 8357-8360.	1.1	8
223	Effect of ion bombardment on deep photoluminescence bands inp-type boron-modulation-doped Si layers grown by molecular-beam epitaxy. Physical Review B, 1995, 52, 12006-12012.	1.1	8
224	Nonradiative defects in Si and SiGe/Si heterostructures grown by molecular beam epitaxy. Applied Physics Letters, 1996, 68, 1256-1258.	1.5	8
225	Postgrowth hydrogen treatments of nonradiative defects in low-temperature molecular beam epitaxial Si. Applied Physics Letters, 1997, 70, 369-371.	1.5	8
226	Electron-paramagnetic-resonance studies of defects in electron-irradiated p-type 4H and 6H SiC. Physica B: Condensed Matter, 1999, 273-274, 655-658.	1.3	8
227	The 3.466 eV Bound Exciton in GaN. Physica Status Solidi (B): Basic Research, 2001, 228, 489-492.	0.7	8
228	The Neutral Silicon Vacancy in SiC: Ligand Hyperfine Interaction. Materials Science Forum, 2002, 389-393, 501-504.	0.3	8
229	Temperature behavior of the GaNP band gap energy. Solid-State Electronics, 2003, 47, 493-496.	0.8	8
230	Band alignment in GaInNPâˆ•GaAs heterostructures grown by gas-source molecular-beam epitaxy. Applied Physics Letters, 2005, 86, 261904.	1.5	8
231	Radiative recombination of GaInNP alloys lattice matched to GaAs. Applied Physics Letters, 2006, 88, 011919.	1.5	8
232	Impact of the strained SiGe source/drain on hot carrier reliability for 45nmâ€ˆp-type metal-oxide-semiconductor field-effect transistors. Applied Physics Letters, 2008, 92, .	1.5	8
233	Understanding and optimizing spin injection in self-assembled InAs/GaAs quantum-dot molecular structures. Nano Research, 2016, 9, 602-611.	5.8	8
234	Electronic properties of a complex Cu-related acceptor with a bound exciton at 2.3423 eV in ZnTe. Physical Review B, 1987, 35, 5714-5721.	1.1	7

#	Article	IF	Citations
235	Effects of a hot two-dimensional electron gas on optical properties of modulation-doped GaAs/AlGaAs heterostructures. Semiconductor Science and Technology, 1992, 7, B253-B255.	1.0	7
236	S-Cu-related metastable complex defect in Si by optical detection of magnetic resonance. Physical Review B, 1994, 50, 7365-7370.	1.1	7
237	Shallow excited states of deep luminescent centers in silicon. Solid State Communications, 1995, 93, 415-418.	0.9	7
238	Transfer mechanism between pseudodonor excited singlet and triplet states of the S-Cu complex defect in silicon. Physical Review B, 1995, 52, 8848-8853.	1.1	7
239	Properties of Er-related emission in in situ doped Si epilayers grown by molecular beam epitaxy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1998, 16, 1732.	1.6	7
240	Effect of zinc substitution on internal friction in YBCO superconductors. Superconductor Science and Technology, 1999, 12, 645-648.	1.8	7
241	Nature and Formation of Non-Radiative Defects in GaNAs And InGaAsN. Materials Research Society Symposia Proceedings, 2001, 692, 1.	0.1	7
242	Electronic Structure of Deep Defects in SiC. Advanced Texts in Physics, 2004, , 461-492.	0.5	7
243	Effect of nitrogen ion bombardment on defect formation and luminescence efficiency of GaNP epilayers grown by molecular-beam epitaxy. Applied Physics Letters, 2006, 88, 101904.	1.5	7
244	Spin Dynamics in ZnO-Based Materials. Journal of Superconductivity and Novel Magnetism, 2010, 23, 161-165.	0.8	7
245	Room-temperature spin injection and spin loss across a GaNAs/GaAs interface. Applied Physics Letters, 2011, 98, 012112.	1.5	7
246	Room temperature spin filtering effect in GaNAs: Role of hydrogen. Applied Physics Letters, 2011, 99, 152109.	1.5	7
247	Optical properties of GaP/GaNP core/shell nanowires: a temperature-dependent study. Nanoscale Research Letters, 2013, 8, 239.	3.1	7
248	Exciton Fine-Structure Splitting in Self-Assembled Lateral InAs/GaAs Quantum-Dot Molecular Structures. ACS Nano, 2015, 9, 5741-5749.	7.3	7
249	Effect of exciton transfer on recombination dynamics in vertically nonuniform GaAsSb epilayers. Applied Physics Letters, 2019, 114, .	1.5	7
250	Band Structure of Wurtzite GaBiAs Nanowires. Nano Letters, 2019, 19, 6454-6460.	4.5	7
251	Cyclotron Resonance Studies of Effective Masses and Band Structure in SiC. Advanced Texts in Physics, 2004, , 437-460.	0.5	7
252	Spectroscopy of Impurities and Complex Defects in Silicon in Zlectric and Microwave Fields. Materials Research Society Symposia Proceedings, 1987, 104, 117.	0.1	6

#	Article	IF	Citations
253	Metastable chalcogen-related luminescent centers in silicon. Physical Review B, 1994, 49, 1662-1667.	1.1	6
254	Optically Detected Magnetic Resonance Studies of Non-Radiative Recombination Centres in 6H SiC. Materials Science Forum, 1998, 264-268, 599-602.	0.3	6
255	The Carbon Vacancy Pair in 4H and 6H SiC. Materials Science Forum, 2000, 338-342, 821-824.	0.3	6
256	Properties of GaAsN/GaAs quantum wells studied by optical detection of cyclotron resonance. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 82, 218-220.	1.7	6
257	On the spin injection in ZnMnSe/ZnCdSe heterostructures. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 538-541.	1.3	6
258	Magnetic resonance signatures of grown-in defects in GaInNP alloys grown on a GaAs substrate. Applied Physics Letters, 2005, 86, 222110.	1.5	6
259	Transition Metal Doped ZnO for Spintronics. Materials Research Society Symposia Proceedings, 2007, 999, 1.	0.1	6
260	Metamorphic InGaAs quantum wells for light emission at 1.3â€“1.6Âμm. Thin Solid Films, 2007, 515, 4348-4351.	0.8	6
261	Effects of P implantation and post-implantation annealing on defect formation in ZnO. Journal of Applied Physics, 2012, 111, 043520.	1.1	6
262	Cathodoluminescence characterization of ZnO tetrapod structures. Thin Solid Films, 2013, 543, 114-117.	0.8	6
263	Size dependence of electron spin dephasing in InGaAs quantum dots. Applied Physics Letters, 2015, 106, 093109.	1.5	6
264	Thermal stability of the prominent compensating (AlZnâ€“VZn) center in ZnO. Journal of Applied Physics, 2016, 119, 105702.	1.1	6
265	N -induced Quantum Dots in GaAs/Ga(N,As) Core/Shell Nanowires: Symmetry, Strain, and Electronic Structure. Physical Review Applied, 2018, 10, .	1.5	6
266	Increasing N content in GaNAsP nanowires suppresses the impact of polytypism on luminescence. Nanotechnology, 2019, 30, 405703.	1.3	6
267	Self-assembled nanodisks in coaxial GaAs/GaAsBi/GaAs coreâ€“multishell nanowires. Nanoscale, 2020, 12, 20849-20858.	2.8	6
268	Effects of thermal annealing on localization and strain in core/multishell GaAs/GaNAs/GaAs nanowires. Scientific Reports, 2020, 10, 8216.	1.6	6
269	An Efficient Deep-Subwavelength Second Harmonic Nanoantenna Based on Surface Plasmon-Coupled Dilute Nitride GaNP Nanowires. Nano Letters, 2021, 21, 3426-3434.	4.5	6
270	Optically Detected Magnetic Resonance of Defects in Semiconductors. Progress in Theoretical Chemistry and Physics, 2003, , 601-625.	0.2	6

#	Article	IF	Citations
271	Optical properties of electron-irradiated GaN. MRS Internet Journal of Nitride Semiconductor Research, 1998, 3, 1.	1.0	6
272	Direct evidence for efficient energy transfer from N-related defects toPGaantisite complexes in GaP from optically detected magnetic resonance. Physical Review B, 1987, 36, 7755-7757.	1.1	5
273	Effects of interlevel coupling on optically detected magnetic resonance spectra for complex defects in semiconductors. Physical Review B, 1988, 38, 12660-12663.	1.1	5
274	Investigation of the (Cu-Li)-related 2.172-eV bound exciton in GaP with optically detected magnetic resonance. Physical Review B, 1988, 38, 1191-1196.	1.1	5
275	Intensity of exciton luminescence in silicon in a weak magnetic field. Physical Review B, 1990, 42, 5120-5125.	1.1	5
276	Direct Determination of the Electron-Electron-Hole Auger Threshold Energy in Silicon. Physical Review Letters, 1994, 73, 3258-3261.	2.9	5
277	Optically detected cyclotron-resonance studies of radiative processes inAlxGa1â˜xAs/GaAs high-electron-mobility structures. Physical Review B, 1995, 52, 14688-14692.	1.1	5
278	The orderedâ€“disordered transition in Si deltaâ€doped GaAs. Applied Physics Letters, 1996, 68, 3464-3466.	1.5	5
279	A Deep Photoluminescence Band in 4H SiC Related to the Silicon Vacancy. Materials Science Forum, 1997, 258-263, 685-690.	0.3	5
280	Effect of Electron Irradiation on Optical Properties of Gallium Nitride. Physica Scripta, 1999, T79, 72.	1.2	5
281	ZnMnSe/ZnSSe Type-II semimagnetic superlattices: Growth and magnetoluminescence properties. Semiconductors, 2002, 36, 1288-1293.	0.2	5
282	Defects in dilute nitrides: significance and experimental signatures. IEE Proceedings: Optoelectronics, 2004, 151, 379-384.	0.8	5
283	Zeeman splitting and dynamics of an isoelectronic bound exciton near the band edge of ZnO. Physical Review B, 2012, 86, .	1.1	5
284	Defect properties of ZnO nanowires. , 2014, , .		5
285	Limiting factor of defect-engineered spin-filtering effect at room temperature. Physical Review B, 2014, 89, .	1.1	5
286	Coreâ€“shell carrier and exciton transfer in GaAs/GaNAs coaxial nanowires. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2016, 34, 04J104.	0.6	5
287	Identification of a Nitrogen-related acceptor in ZnO nanowires. Nanoscale, 2019, 11, 10921-10926.	2.8	5
288	Effects of growth temperature and thermal annealing on optical quality of GaNAs nanowires emitting in the near-infrared spectral range. Nanotechnology, 2020, 31, 065702.	1.3	5

#	Article	IF	Citations
289	Effects of Bi incorporation on recombination processes in wurtzite GaBiAs nanowires. Nanotechnology, 2020, 31, 225706.	1.3	5
290	Time-resolved zero-field optically detected magnetic-resonance study of the (Cu-Li)Vneutral defect complex in GaP. Physical Review B, 1990, 42, 1684-1689.	1.1	4
291	ODMR and Electron Spin Echo Studies on the Non-Radiative Triplet State of the (V-O)Â° Defect in Silicon. Materials Science Forum, 1992, 83-87, 357-362.	0.3	4
292	The Configurational Change of a Metastable S-Cu Defect in Silicon. Materials Science Forum, 1994, 143-147, 1179-1184.	0.3	4
293	Chenet al.Reply. Physical Review Letters, 1995, 75, 3963-3963.	2.9	4
294	Influence of growth conditions on the formation of deep photoluminescence bands in MBE-grown Si layers and SiGe/Si quantum structures. Applied Surface Science, 1996, 102, 293-297.	3.1	4
295	Fermi-edge singularity inp-type modulation-doped SiGe quantum wells. Physical Review B, 1996, 53, R1701-R1704.	1.1	4
296	Effects of microwave fields on recombination processes in 4H and 6H SiC. Journal of Applied Physics, 1997, 81, 1929-1932.	1.1	4
297	Applications of defect engineering in InP-based structures. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2000, 75, 103-109.	1.7	4
298	Strain relaxation in GaNxP1â^'x alloy: effect on optical properties. Physica B: Condensed Matter, 2001, 308-310, 106-109.	1.3	4
299	Semimagnetic ZnMnSe/CdSe Fractional Monolayer Superlattice as an Injector of Spin-Polarized Carriers. Physica Status Solidi (B): Basic Research, 2002, 229, 765-768.	0.7	4
300	Origin of bandgap bowing in GaNP alloys. IEE Proceedings: Optoelectronics, 2004, 151, 389-392.	0.8	4
301	Electrical and luminescent properties and the spectra of deep centers in GaMnN/InGaN light-emitting diodes. Journal of Electronic Materials, 2004, 33, 241-247.	1.0	4
302	Investigation of a GaMnN/GaN/InGaN structure for spin LED. AIP Conference Proceedings, 2005, , .	0.3	4
303	Optical characterization studies of grown-in defects in ZnO epilayers grown by molecular beam epitaxy. Physica B: Condensed Matter, 2007, 401-402, 413-416.	1.3	4
304	Spin-Conserving Tunneling of Excitons in Diluted Magnetic Semiconductor Double Quantum Wells. Japanese Journal of Applied Physics, 2008, 47, 3533-3536.	0.8	4
305	Efficiency of spin injection in novel InAs quantum dot structures: exciton vs. free carrier injection. Journal of Physics: Conference Series, 2010, 245, 012044.	0.3	4
306	Effects of a longitudinal magnetic field on spin injection and detection in InAs/GaAs quantum dot structures. Journal of Physics Condensed Matter, 2012, 24, 145304.	0.7	4

#	Article	IF	Citations
307	Temperature dependence of dynamic nuclear polarization and its effect on electron spin relaxation and dephasing in InAs/GaAs quantum dots. Applied Physics Letters, 2012, 100, .	1.5	4
308	Effects of hydrogenation on non-radiative defects in GaNP and GaNAs alloys: An optically detected magnetic resonance study. Journal of Applied Physics, 2012, 111, 023501.	1.1	4
309	Antiferromagnetic interaction in coupled CdSe/ZnMnSe quantum dot structures. Applied Physics Letters, 2012, 101, 052405.	1.5	4
310	The Hanle effect and electron spin polarization in InAs/GaAs quantum dots up to room temperature. Nanotechnology, 2012, 23, 135705.	1.3	4
311	Structural properties of GaNAs nanowires probed by micro-Raman spectroscopy. Semiconductor Science and Technology, 2016, 31, 025002.	1.0	4
312	Formation, electronic structure, and optical properties of self-assembled quantum-dot single-photon emitters in Ga(N,As,P) nanowires. Physical Review Materials, 2020, 4, .	0.9	4
313	Optical characterization of a deep (Cu-C)-related complex defect in GaP. Physical Review B, 1989, 39, 3153-3158.	1.1	3
314	Optically detected magnetic resonance of a thermally induced deep center in electron-irradiated silicon. Physical Review B, 1989, 40, 10013-10016.	1.1	3
315	Hot-Carrier Effects on Optical Properties of GaAs/Al_xGai_{1-x}As Quantum Wells. Materials Research Society Symposia Proceedings, 1989, 160, 707.	0.1	3
316	Defect annealing in electron-irradiated boron-doped silicon. Physical Review B, 1990, 41, 1019-1027.	1.1	3
317	Optically Detected Magnetic Resonance Studies of Bound Exciton Triplets for Complex Defects in GaP. Materials Science Forum, 1989, 38-41, 769-774.	0.3	3
318	Magnetic Resonance Techniques for Excited State Spectroscopy of Defects in Silicon. Materials Science Forum, 1994, 143-147, 1345-1352.	0.3	3
319	Optically detected magnetic resonance studies of defects in 3C SiC epitaxial layers. Diamond and Related Materials, 1997, 6, 1381-1384.	1.8	3
320	Photoluminescence upconversion in 4Hâ€“SiC. Applied Physics Letters, 2002, 81, 2547-2549.	1.5	3
321	Exciton Spin Manipulation in ZnMnSe-Based Structures. Journal of Superconductivity and Novel Magnetism, 2003, 16, 399-402.	0.5	3
322	Hydrogen-related effects in diluted nitrides. Physica B: Condensed Matter, 2003, 340-342, 371-376.	1.3	3
323	Magneto-photoluminescence studies of diluted magnetic semiconductor type-II quantum wells ZnMnSe/ZnSSe. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 17, 352-354.	1.3	3
324	Resonant suppression of exciton spin relaxation in Zn0.96Mn0.04Se/CdSe superlattices. Journal of Applied Physics, 2003, 93, 7352-7354.	1.1	3

#	Article	IF	Citations
325	Effects of rapid thermal annealing on optical quality of GaNP alloys. IEE Proceedings: Optoelectronics, 2004, 151, 335-337.	0.8	3
326	Exciton magnetic polarons in a type II ZnMnSe/ZnSSe superlattice. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 847-850.	0.8	3
327	Spin injection and spin loss in GaMnN/InGaN Light-Emitting Diodes. AIP Conference Proceedings, 2005, , .	0.3	3
328	Material properties of dilute nitrides: Ga(In)NAs and Ga(In)NP. Journal of Crystal Growth, 2006, 288, 7-11.	0.7	3
329	Optical Characterization of Zn1-xCdxO Alloys Grown by Molecular-Beam Epitaxy. ECS Transactions, 2006, 3, 391-398.	0.3	3
330	Optically detected cyclotron resonance studies of InxGa1â^'xNyAs1â^'yâ^•GaAs quantum wells sandwiched between type-II AlAsâ^•GaAs superlattices. Journal of Applied Physics, 2007, 101, 073705.	1.1	3
331	Effect of thermal annealing on defects in post-growth hydrogenated GaNP. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 561-563.	0.8	3
332	Effect of a Phonon Bottleneck on Exciton and Spin Generation in Self-Assembled <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mi>In</mml:mi></mml:mrow><mml:mrow><mml:mn>1</mml:mn><mml Quantum Dots. Physical Review Applied, 2018, 9, .	1.5	3
333	Outermost AlGaO x native oxide as a protection layer for GaAs/AlGaAs core-multishell nanowires. Applied Physics Express, 2020, 13, 075003.	1.1	3
334	Molecular beam epitaxial growth of GaAs/GaNAsBi coreâ€"multishell nanowires. Applied Physics Express, 2021, 14, 115002.	1.1	3
335	Optically Detected Magnetic Resonance Studies of Complex Antisite-Related Defects in Bulk Lec GaP. Materials Research Society Symposia Proceedings, 1987, 104, 467.	0.1	2
336	Electronic structure of complex defects in semiconductors from luminescence perturbation spectroscopy. Journal of Luminescence, 1988, 40-41, 59-63.	1.5	2
337	Spin-forbidden Î"ms=2 transitions in the optically detected magnetic-resonance spectra of excitons bound at complex neutral defects in GaP. Physical Review B, 1988, 37, 8795-8804.	1.1	2
338	A New Defect Observed in Annealed Phosphorus-Doped Electron-Irradiated Silicon. Materials Science Forum, 1992, 83-87, 333-338.	0.3	2
339	Electronic Structure of P_{In} Antisite in InP. Materials Science Forum, 1994, 143-147, 211-216.	0.3	2
340	Properties of Resonant Localized Donor Level in Low-Temperature-Grown InP. Materials Science Forum, 1994, 143-147, 1081-1086.	0.3	2
341	A Metastable Selenium-Related Center in Silicon. Materials Science Forum, 1994, 143-147, 159-164.	0.3	2
342	Application of the ODCR experiment to the identification of radiative recombination processes. Journal of Luminescence, 1994, 60-61, 52-55.	1.5	2

#	Article	IF	Citations
343	Important Nonradiative Grown-In Defects in MBE-Grown Si and SiGe/Si Heterostructures. Materials Science Forum, 1995, 196-201, 473-478.	0.3	2
344	Defects In Low Temperature Mbe-Grown Si And Sige/Si Structures. Materials Research Society Symposia Proceedings, 1996, 442, 355.	0.1	2
345	Electronic structure of the 0.88-eV luminescence center in electron-irradiated gallium nitride. Physical Review B, 1999, 60, 1746-1751.	1.1	2
346	Raman Studies of GaNP Alloy. Materials Research Society Symposia Proceedings, 2001, 693, 567.	0.1	2
347	Magneto-photoluminescence studies of Cd(Mn)Se/Zn(Mn)Se diluted magnetic nanostructures. Physica E: Low-Dimensional Systems and Nanostructures, 2001, 10, 362-367.	1.3	2
348	Electronic Structure of the UD3 Defect in 4H- and 6H-SiC. Materials Science Forum, 2002, 389-393, 509-512.	0.3	2
349	Evidence for type I band alignment in GaNAs/GaAs quantum structures by optical spectroscopies. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 1074-1077.	1.3	2
350	Identification of Ga interstitials in GaAlNP. Physica B: Condensed Matter, 2003, 340-342, 466-469.	1.3	2
351	Formation of Ferromagnetic SiC:Mn Phases. Materials Science Forum, 2005, 483-485, 241-244.	0.3	2
352	Magneto-optical spectroscopy of spin injection and spin relaxation in ZnMnSe/ZnCdSe and GaMnN/InGaN spin light-emitting structures. Physica Status Solidi (A) Applications and Materials Science, 2007, 204, 159-173.	0.8	2
353	Sub-millisecond dynamic nuclear spin hyperpolarization in a semiconductor: A case study from PInantisite in InP. Physical Review B, 2012, 86, .	1.1	2
354	Dual-wavelength excited photoluminescence spectroscopy of deep-level hole traps in Ga(In)NP. Journal of Applied Physics, 2015, 117, 015701.	1.1	2
355	Phosphorescence of CdS nanoparticles in polymer matrix as an indication of host-guest interaction. Materials Chemistry and Physics, 2016, 177, 379-383.	2.0	2
356	Scattering symmetry-breaking induced spin photocurrent from out-of-plane spin texture in a 3D topological insulator. Scientific Reports, 2020, 10, 10610.	1.6	2
357	Identifying a Generic and Detrimental Role of Fano Resonance in Spin Generation in Semiconductor Nanostructures. Physical Review Letters, 2021, 127, 127401.	2.9	2
358	Defects in Dilute Nitrides. Acta Physica Polonica A, 2005, 108, 571-579.	0.2	2
359	Role of the Substitutional Oxygen Donor in the Residual N-Type Conductivity in GaN. MRS Internet Journal of Nitride Semiconductor Research, 1999, 4, 514-519.	1.0	2
360	Gallium vacanciesâ€"common non-radiative defects in ternary GaAsP and quaternary GaNAsP nanowires. Nano Express, 2020, 1, 020022.	1.2	2

#	Article	IF	Citations
361	Electromagnetic instability in interpenetrating electron-ion plasmas. Physics of Fluids, 1973, 16, 277.	1.4	1
362	Electronic Structure of Neutral Complex Defects in Silicon. Materials Science Forum, 1986, 10-12, 97-102.	0.3	1
363	ELECTRONIC STRUCTURE OF BOUND EXCITONS IN SEMICONDUCTORS. , 1987, , 256-285.		1
364	â€˜â€˜Forbiddenâ€™â€™ electronic- and nuclear-spin transitions in optically detected magnetic resonance spectra of deep complex defects in GaP. Physical Review B, 1988, 37, 6555-6558.	1.1	1
365	Optical detection of chaotic oscillations owing to impact ionization of donors by hot carriers in GaInAs. Semiconductor Science and Technology, 1992, 7, B483-B485.	1.0	1
366	Observation of Rapid Direct Charge Transfer between Deep Defects in Silicon. Materials Science Forum, 1993, 143-147, 1371-1374.	0.3	1
367	Optically Detected Cyclotron Resonance for Defect Characterization. Materials Science Forum, 1994, 143-147, 1353-1358.	0.3	1
368	Efficient Nonradiative Recombination Centers in MBE-Grown Si and SiGe/Si Heterostructures. Materials Research Society Symposia Proceedings, 1995, 378, 135.	0.1	1
369	Radiative Recombination Processes in Boron Modulation-Doped SiGe Quantum Wells. Materials Research Society Symposia Proceedings, 1995, 378, 881.	0.1	1
370	Deep Photoluminescence Bands in Mbe Grown Si and Sige.. Materials Research Society Symposia Proceedings, 1995, 379, 405.	0.1	1
371	Efficient excitation transfer in silicon studied by Fourier transform photoluminescence excitation spectroscopy. Applied Physics Letters, 1995, 66, 1498-1500.	1.5	1
372	Intense photoluminescence observed in modulation doped Si/SiGe quantum well structures. Applied Surface Science, 1996, 102, 298-302.	3.1	1
373	Intrinsic Modulation Doping in InP-Based Heterostructures. Materials Science Forum, 1997, 258-263, 805-812.	0.3	1
374	Thermal stability and doping efficiency of intrinsic modulation doping in InP-based structures. Applied Physics Letters, 1999, 75, 1733-1735.	1.5	1
375	Zeeman spectroscopy of the neutral silicon vacancy in 6H and 4H SiC. Physica B: Condensed Matter, 1999, 273-274, 663-666.	1.3	1
376	Magnetooptical Investigations on Electron Irradiated GaN. Physica Scripta, 1999, T79, 53.	1.2	1
377	Bandstructure and Transport Properties of 4H- and 6H-SiC: Optically Detected Cyclotron Resonance Investigations. Materials Science Forum, 2000, 338-342, 559-562.	0.3	1
378	Pâ€“N defect in GaNP studied by optically detected magnetic resonance. Physica B: Condensed Matter, 2003, 340-342, 399-402.	1.3	1

#	Article	IF	Citations
379	InAs/Zn(Mn)Te/Cd(Mn)Se pseudomorphic quantum well structures for spintronic applications. Physica Status Solidi (B): Basic Research, 2004, 241, 704-707.	0.7	1
380	Optical Study of Spin Injection Dynamics in Double Quantum Wells of II-VI Diluted Magnetic Semiconductors. AIP Conference Proceedings, 2005, , .	0.3	1
381	Ferromagnetism in ZnO Doped with Transition Metal Ions. , 2006, , 555-576.		1
382	Unusual effects of hydrogen on electronic and lattice properties of GaNP alloys. Physica B: Condensed Matter, 2006, 376-377, 568-570.	1.3	1
383	Transient photoluminescence spectroscopy of spin injection dynamics in double quantum wells of diluted magnetic semiconductors. Journal of Luminescence, 2006, 119-120, 418-422.	1.5	1
384	On a possible origin of the 2.87 eV optical transition in GaNP. Journal of Physics Condensed Matter, 2006, 18, 449-457.	0.7	1
385	Investigation of the Electronic Structure of the UD-4 Defect in 4H-SiC by Optical Techniques. Materials Science Forum, 2006, 527-529, 461-464.	0.3	1
386	Magneto-optical and tunable laser excitation spectroscopy of spin-injection and spin loss from Zn(Cd)MnSe diluted magnetic quantum well to CdSe non-magnetic quantum dots. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2008, 147, 262-266.	1.7	1
387	Optical and electronic properties of GaInNP alloys â€“ a new material system for lattice matching to GaAs. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 101-106.	0.8	1
388	Transfer dynamics of spin-polarized excitons into semiconductor quantum dots. Journal of Luminescence, 2009, 129, 1927-1930.	1.5	1
389	Magneto-optical properties and recombination dynamics of isoelectronic bound excitons in ZnO. , 2014, , .		1
390	Spin dynamics of isoelectronic bound excitons in ZnO. Physical Review B, 2014, 89, .	1.1	1
391	Novel GaNAs and GaNP-based nanowires â€” Promising materials for optoelectronics and photonics. , 2016, , .		1
392	Novel GaP/GaNP core/shell nanowires for optoelectronics and photonics. , 2016, , .		1
393	Unintentional nitrogen incorporation in ZnO nanowires detected by electron paramagnetic resonance spectroscopy. Physica Status Solidi C: Current Topics in Solid State Physics, 2016, 13, 572-575.	0.8	1
394	Photon upconversion promoted by defects in low-dimensional semiconductor nanostructures. , 2018, , 189-210.		1
395	Defects in one-dimensional nanowires. , 2018, , 63-85.		1
396	Efficient Auger Charge-Transfer Processes in ZnO. Physical Review Applied, 2018, 9, .	1.5	1

#	Article	IF	Citations
397	Oblique Nuclear Quadrupole Interaction in Self-Assembled Structures Based on Semiconductor Quantum Dots. Physical Review Applied, 2020, 14, .	1.5	1
398	Exciton generation and recombination dynamics of quantum dots embedded in GaNAsP nanowires. Physical Review B, 2021, 103, .	1.1	1
399	The 3.466 eV Bound Exciton in GaN. , 2001, 228, 489.		1
400	Effective Masses in SiC Determined by Cyclotron Resonance Experiments. Physica Status Solidi A, 1997, 162, 79.	1.7	1
401	Optical Detection of Magnetic Resonance (ODMR) Studies of the Electronic Structure of Complex Defects in GaP. Materials Research Society Symposia Proceedings, 1987, 104, 443.	0.1	0
402	Complex defects in gap studied by optically detected magnetic resonance (ODMR). Journal of Luminescence, 1988, 40-41, 337-338.	1.5	0
403	Optically Detected Magnetic Resonance of a Hydrogen-Related Complex Defect in Silicon. Materials Research Society Symposia Proceedings, 1989, 163, 377.	0.1	0
404	Radiative recombination processes in p-type modulation-doped SiGe quantum wells and Si epilayers. Journal of Crystal Growth, 1995, 157, 362-366.	0.7	0
405	Defect Formation and Recombination Processes in p-Type Modulation-Doped Si Epilayers. Materials Science Forum, 1995, 196-201, 479-484.	0.3	0
406	Intrinsic N-Type Modulation Doping in Inp-Based Heterostructures. Materials Research Society Symposia Proceedings, 1996, 421, 21.	0.1	0
407	Optical properties of boron modulation-doped SiGe quantum wells and Si thin films. Solid-State Electronics, 1996, 40, 53-57.	0.8	0
408	Important defect aspects in optoelectronic applications of Si- and SiGe/Si-heterostructures. Applied Surface Science, 1996, 102, 279-282.	3.1	0
409	The Role of Non-Radiative Defects in Thermal Quenching of Luminescence in SiGe/Si Structures Grown by Molecular Beam Epitaxy. Materials Science Forum, 1997, 258-263, 139-144.	0.3	0
410	Mbe Growth And Characterization Of Er/O And Er/F Doped Si Light Emitting Structures. Materials Research Society Symposia Proceedings, 1997, 486, 133.	0.1	0
411	On the improvement in thermal quenching of luminescence in SiGe/Si structures grown by molecular beam epitaxy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1998, 16, 1928.	1.6	0
412	Influence Of Growth Conditions On The Thermal Quenching Of Photoluminescence From Sige/Si Quantum Structures. Materials Research Society Symposia Proceedings, 1998, 533, 295.	0.1	0
413	Role of the Substitutional Oxygen Donor in the Residual N-Type Conductivity in GaN. Materials Research Society Symposia Proceedings, 1998, 537, 1.	0.1	0
414	Intrinsic modulation doping in InP-based structures: properties relevant to device applications. Journal of Crystal Growth, 1999, 201-202, 786-789.	0.7	0

#	Article	IF	Citations
415	Transport Properties of Intrinsically and Extrinsically Modulation Doped InP/InGaAs Heterostructures. Physica Scripta, 1999, T79, 103.	1.2	0
416	Optically detected magnetic resonance of semiconductor thin films and layered structures. , 2000, 4086, 44.		0
417	Optical and electronic properties of GaNAs/GaAs structures. , 0, , .		0
418	Hole Effective Masses in 4H SiC Determined by Optically Detected Cyclotron Resonance. Materials Science Forum, 2000, 338-342, 563-566.	0.3	0
419	Magneto-optical spectroscopy of defects in wide bandgap semiconductors: GaN and SiC. , 0, , .		0
420	Spin Polarization and Injection in ZnMnSe/ZnCdSe Heterostructures. Materials Research Society Symposia Proceedings, 2001, 690, F1.7.1.	0.1	0
421	Photoluminescence Up-Conversion Processes in SiC. Materials Science Forum, 2003, 433-436, 309-312.	0.3	0
422	Role of hydrogen in improving optical quality of GaNAs alloys. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 20, 313-316.	1.3	0
423	High Energy Optical Transitions in Ga(PN): Contribution from Perturbed Valence Band. AIP Conference Proceedings, 2005, , .	0.3	0
424	New Insight into the Electronic Properties of GaNP Alloys. AIP Conference Proceedings, 2005, , .	0.3	0
425	Ga-interstitial related defects in Ga(Al)NP. AIP Conference Proceedings, 2005, , .	0.3	0
426	Spin depolarization in semiconductor spin detectors. , 2006, , .		0
427	Signatures of grown-in defects in GaInNP alloys grown on a GaAs substrate from magnetic resonance studies. Physica B: Condensed Matter, 2006, 376-377, 571-574.	1.3	0
428	Transient Spectroscopy of Optical Spin Injection in ZnMnSe/ZnCdSe Quantum Structures. Journal of Superconductivity and Novel Magnetism, 2006, 18, 371-373.	0.5	0
429	Intrinsic Paramagnetic Defects in GaNP Alloys Grown on Silicon. ECS Transactions, 2006, 3, 231-236.	0.3	0
430	Prospects of Potential Semiconductor Spin Detectors. Solid State Phenomena, 2007, 124-126, 839-842.	0.3	0
431	Spin Dynamics of Type-II Excitons in Diluted Magnetic Double Quantum Wells. AIP Conference Proceedings, 2007, , .	0.3	0
432	Role of Nitrogen In Photoluminescence Up-conversion In GaInNP/GaAs Heterostructures. AIP Conference Proceedings, 2007, , .	0.3	0

#	Article	IF	Citations
433	Optically detected cyclotron resonance studies of InGaNAs/GaAs structures. AIP Conference Proceedings, 2007, , .	0.3	0
434	Spin injection in a coupled system of a diluted magnetic semiconductor Zn0.80Mn0.20Se and self-assembled quantum dots of CdSe. Superlattices and Microstructures, 2008, 43, 615-619.	1.4	0
435	Effect of growth conditions on grownâ€in defect formation and luminescence efficiency in Ga(In)NP epilayers grown by molecularâ€beam epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 460-463.	0.8	0
436	Effects of grown-in defects on electron spin polarization in dilute nitride alloys. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1529-1531.	0.8	0
437	Spin resonance spectroscopy of grown-in defects in Ga(In)NP alloys. Superlattices and Microstructures, 2008, 43, 620-625.	1.4	0
438	Propagation dynamics of exciton spins in a highâ€density semiconductor quantum dot system. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 50-52.	0.8	0
439	Long delays of light in ZnO caused by excitonâ€polariton propagation. Physica Status Solidi (B): Basic Research, 2012, 249, 1307-1311.	0.7	0
440	Back Cover: Long delays of light in ZnO caused by exciton-polariton propagation (Phys. Status Solidi B) Tj ETQq0 0 0 rgBT /Overlock 10 T	0.7	0
441	Characterization of quantum dot-like emission from GaAs/GaNAs core/shell nanowires. , 2016, , .		0
442	Spin injection and detection in semiconductor nanostructures. , 2016, , .		0
443	Spin injection loss in self-assembled InAs/GaAs quantum dot structures from disordered barrier layers. , 2016, , .		0
444	Room Temperature Defect-Engineered Spin Functionalities: Concept and Optimization. , 2017, , 33-54.		0
445	Defect-enabled room-temperature spin functionalities in a nonmagnetic semiconductor. , 2018, , 265-284.		0
446	Disorder-Activated Resonant Raman Scattering in GaNAs/GaAs Structures. Springer Proceedings in Physics, 2001, , 73-74.	0.1	0
447	Recombination Processes of GaNAs/GaAs structures: Effect of Rapid Thermal Annealing. Springer Proceedings in Physics, 2001, , 559-560.	0.1	0
448	On the Origin of Light Emission in GaNxP1-x. Materials Research Society Symposia Proceedings, 2002, 722, 421.	0.1	0
449	Identification Of Point Defects In Ga(Al)NAs Alloys. AIP Conference Proceedings, 2007, , .	0.3	0
450	Transfer Dynamics of Spin-Polarized Excitons in ZnCdMnSe/ZnCdSe Double Quantum Wells. Journal of the Korean Physical Society, 2008, 53, 167-170.	0.3	0

#	Article	IF	Citations
451	Spin-Injection Dynamics and Effects of Spin Relaxation in Self-Assembled Quantum Dots of CdSe. Journal of the Korean Physical Society, 2008, 53, 163-166.	0.3	0
452	Efficient Spin Filter Based on Non-Magnetic Semiconductor GaNAs. , 2009, , .		0
453	Impact Ionization Driven Chaotic Photoluminescence Oscillations in Ga0.47In0.53As. Acta Physica Polonica A, 1991, 80, 271-274.	0.2	0
454	Optically Detected Magnetic Resonance Studies of Te-Related Shallow Donors in AlxGa1-xAs. Acta Physica Polonica A, 1991, 80, 341-344.	0.2	0
455	AlGaAs to GaAs Energy Transfer Mechanisms in AlGaAs/GaAs Structures. Acta Physica Polonica A, 1992, 82, 713-716.	0.2	0
456	Spin-Polarized Light Emitting Self-Assembled InAs/GaAs Quantum-Dot Molecular Structures: The Dominant Mechanism for Spin Loss during Spin Injection. ECS Meeting Abstracts, 2016, , .	0.0	0
457	GaNAs-Based Nanowires for Near-Infrared Optoelectronics. , 2017, , 133-159.		0
458	Novel GaNP Nanowires for Advanced Optoelectronics and Photonics. , 2017, , 107-132.		0
459	Optical and Electronic Properties of GaInNP Alloys: A New Material for Lattice Matching to GaAs. , 2008, , 301-316.		0